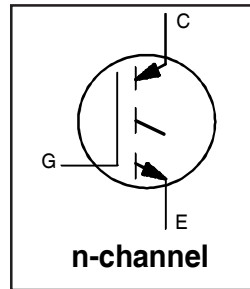


# IRG4PC50WPbF

## INSULATED GATE BIPOLAR TRANSISTOR

### Features

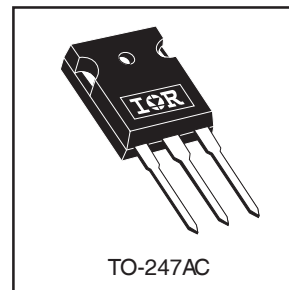
- Designed expressly for Switch-Mode Power Supply and PFC (power factor correction) applications
- Industry-benchmark switching losses improve efficiency of all power supply topologies
- 50% reduction of Eoff parameter
- Low IGBT conduction losses
- Latest-generation IGBT design and construction offers tighter parameters distribution, exceptional reliability
- Lead-Free



$V_{CES} = 600V$
$V_{CE(on) max.} = 2.30V$
@ $V_{GE} = 15V, I_C = 27A$

### Benefits

- Lower switching losses allow more cost-effective operation than power MOSFETs up to 150 kHz ("hard switched" mode)
- Of particular benefit to single-ended converters and boost PFC topologies 150W and higher
- Low conduction losses and minimal minority-carrier recombination make these an excellent option for resonant mode switching as well (up to >300 kHz)



### Absolute Maximum Ratings

	Parameter	Max.	Units
$V_{CES}$	Collector-to-Emitter Breakdown Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	55	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	27	
$I_{CM}$	Pulsed Collector Current ①	220	
$I_{LM}$	Clamped Inductive Load Current ②	220	
$V_{GE}$	Gate-to-Emitter Voltage	$\pm 20$	V
$E_{ARV}$	Reverse Voltage Avalanche Energy ③	170	mJ
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	200	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	78	
$T_J$	Operating Junction and Storage Temperature Range	-55 to + 150	°C
$T_{STG}$	Soldering Temperature, for 10 seconds	300 (0.063 in. (1.6mm from case )	
	Mounting torque, 6-32 or M3 screw.	10 lbf•in (1.1N•m)	

### Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	---	0.64	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.24	---	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	---	40	
Wt	Weight	6 (0.21)	---	

# IRG4PC50WPbF

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$
$V_{(BR)CES}$	Emitter-to-Collector Breakdown Voltage ④	18	—	—	V	$V_{GE} = 0V, I_C = 1.0A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.41	—	V/°C	$V_{GE} = 0V, I_C = 5.0mA$
$V_{CE(ON)}$	Collector-to-Emitter Saturation Voltage	—	1.93	2.3	V	$I_C = 27A$ $I_C = 55A$ $I_C = 27A, T_J = 150^\circ\text{C}$ $V_{GE} = 15V$ See Fig.2, 5
		—	2.25	—		
		—	1.71	—		
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		$V_{CE} = V_{GE}, I_C = 250\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-11	—	mV/°C	$V_{CE} = V_{GE}, I_C = 1.0mA$
$g_{fe}$	Forward Transconductance ⑤	27	41	—	S	$V_{CE} = 100V, I_C = 27A$
$I_{CES}$	Zero Gate Voltage Collector Current	—	—	250	$\mu A$	$V_{GE} = 0V, V_{CE} = 600V$ $V_{GE} = 0V, V_{CE} = 10V, T_J = 25^\circ\text{C}$ $V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$
		—	—	2.0		
		—	—	5000		
$I_{GES}$	Gate-to-Emitter Leakage Current	—	—	$\pm 100$	nA	$V_{GE} = \pm 20V$

## Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$Q_g$	Total Gate Charge (turn-on)	—	180	270	nC	$I_C = 27A$ $V_{CC} = 400V$ $V_{GE} = 15V$ See Fig.8
$Q_{ge}$	Gate - Emitter Charge (turn-on)	—	24	36		
$Q_{gc}$	Gate - Collector Charge (turn-on)	—	63	95		
$t_{d(on)}$	Turn-On Delay Time	—	46	—	ns	$T_J = 25^\circ\text{C}$ $I_C = 27A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 5.0\Omega$ Energy losses include "tail" See Fig. 9, 10, 14
$t_r$	Rise Time	—	33	—		
$t_{d(off)}$	Turn-Off Delay Time	—	120	180		
$t_f$	Fall Time	—	57	86		
$E_{on}$	Turn-On Switching Loss	—	0.08	—	mJ	See Fig. 9, 10, 14
$E_{off}$	Turn-Off Switching Loss	—	0.32	—		
$E_{ts}$	Total Switching Loss	—	0.40	0.5		
$t_{d(on)}$	Turn-On Delay Time	—	31	—	ns	$T_J = 150^\circ\text{C},$ $I_C = 27A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 5.0\Omega$ Energy losses include "tail" See Fig. 10,11, 14
$t_r$	Rise Time	—	43	—		
$t_{d(off)}$	Turn-Off Delay Time	—	210	—		
$t_f$	Fall Time	—	62	—		
$E_{ts}$	Total Switching Loss	—	1.14	—	mJ	
$L_E$	Internal Emitter Inductance	—	13	—	nH	Measured 5mm from package
$C_{ies}$	Input Capacitance	—	3700	—	pF	$V_{GE} = 0V$ $V_{CC} = 30V$ $f = 1.0MHz$ See Fig. 7
$C_{oes}$	Output Capacitance	—	260	—		
$C_{res}$	Reverse Transfer Capacitance	—	68	—		

### Notes:

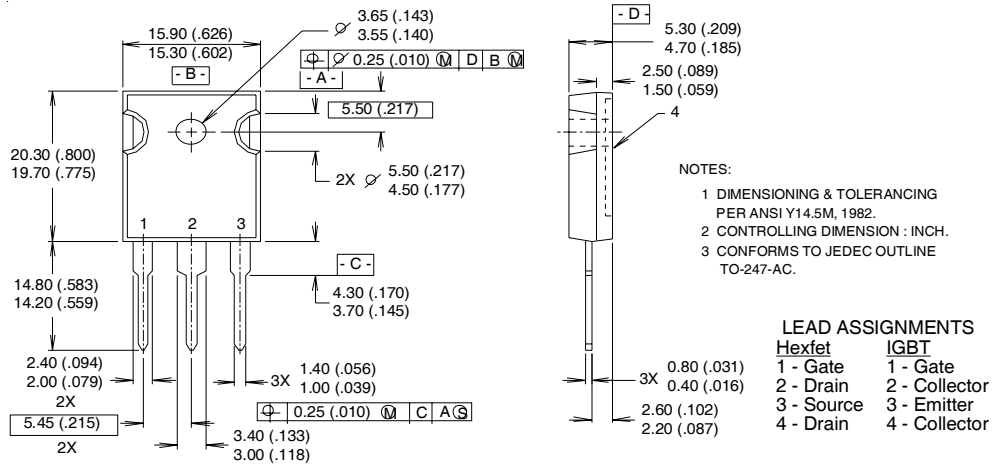
- ① Repetitive rating;  $V_{GE} = 20V$ , pulse width limited by max. junction temperature. ( See fig. 13b )
- ②  $V_{CC} = 80\%(V_{CES}), V_{GE} = 20V, L = 10\mu H, R_G = 5.0\Omega,$  (See fig. 13a)
- ③ Repetitive rating; pulse width limited by maximum junction temperature.
- ④ Pulse width  $\leq 80\mu s$ ; duty factor  $\leq 0.1\%$ .
- ⑤ Pulse width  $5.0\mu s$ , single shot.

# IRG4PC50WPbF



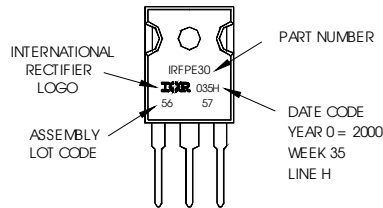
## TO-247AC Package Outline

Dimensions are shown in millimeters (inches)



## TO-247AC Part Marking Information

EXAMPLE: THIS IS AN IRFPE30  
WITH ASSEMBLY  
LOT CODE 5657  
ASSEMBLED ON WW 35, 2000  
IN THE ASSEMBLY LINE "H"  
**Note:** "P" in assembly line  
position indicates "Lead-Free"



Data and specifications subject to change without notice.

